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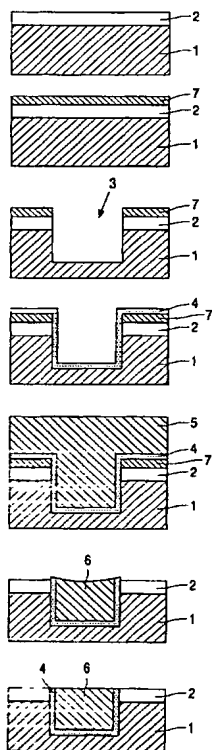
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(54) Title: METHOD FOR FABRICATION OF IN-LAID METAL INTERCONNECTS

(57) **Abstract:** The present invention relates to a method for fabrication of in-laid metal interconnects. The method comprises the steps of providing a substrate with a dielectric material (1) on top thereof, depositing a protection layer (2) on top of the dielectric material, depositing a sacrificial layer (7) on top of the protection layer, the sacrificial layer having a mechanical strength that is lower than the mechanical strength of the protection layer, making an opening (3) through the sacrificial layer, through the protection layer and into the dielectric material, depositing a barrier layer (4) in the opening and on the sacrificial layer, depositing metal material (5) on the barrier layer, the metal material filling the opening, removing portions of the metal material existing beyond the opening by means of polishing, and removing the barrier layer and the sacrificial layer in one polishing step.



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